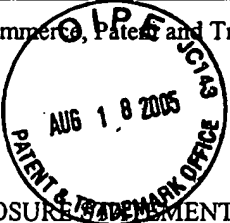
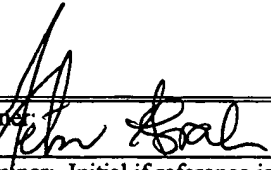
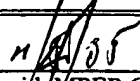
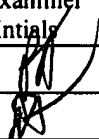
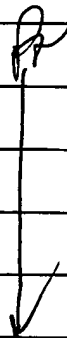


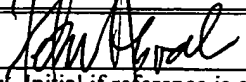
U.S. Department of Commerce, Patent and Trademark Office  INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Application No.:	10/771,593
	Filing Date:	02/02/2004
	First Named Inventor:	Hamza Yilmaz
	Group Art Unit:	2826
	Examiner Name:	Fetsum Abraham
	Confirmation No.:	3820
	Attorney Docket No.:	YMZ004 US

U.S. Patent Documents							
*Examiner Initials		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
Pr	1.	2004/0084721 A1	05/06/2004	Kocon et al.	257	328	11/05/2002
Foreign Patent Documents							
		Document	Date	Country	Class	Subclass	Translation Yes No
✓	2.	EP 1073110 A1	01/31/2001	Europe	21	329	X
	3.	EP 1369927 A2	12/10/2003	Europe	29	78	
	4.	JP 07142713	06/02/1995	Japan	29	78	X
	5.	JP 08102538	04/16/1996	Japan	29	78	X
Non Patent Literature Documents							
✓	6.	Gupta, R.N. et al., A Novel Planarized, Silicon Trench Sidewall Oxide-Merged p-i-n Schottky (TSOX-MPS) Rectifier, IEEE Electron Device Letters, Vol. 20, No. 12, December 1999					
	7.	Chang, H.R. et al., Development and Demonstration of Silicon Carbide (SiC) Motor Drive Inverter Modules, 2003 IEEE 34 th Annual Power Electronics Specialists Conference (PESC) Conference Proceedings, Acapulco, Mexico, 06/15/2003					

Examiner: 	Date Considered: 
* Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication with applicant.	

U.S. Department of Commerce, Patent and Trademark Office INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Application No.:	Unknown
	Filing Date:	Unknown
	First Named Inventor:	Hamza Yilmaz
	Group Art Unit:	Unknown
	Examiner Name:	Unknown
	Confirmation No.:	Unknown
	Attorney Docket No.:	YMZ004 US

U.S. Patent Documents								
*Examiner Initials		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
	1.	5,168,331	12/01/92	Yilmaz	257	331		
	2.	5,216,275	06/01/93	Chen	257	493		
Foreign Patent Documents								
							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
Other Art (Including Author, Title, Date, Pertinent Pages, Etc.)								
	3.	Jongdae Kim et al., "High-Density Trench DMOSFETs Employing Two Step Trench Technique and Trench Contact Structure", ISPSD-2003 Proceedings, pp. 1-4						
	4.	Il-Yong Park et al., "Novel Process Techniques for Fabricating High Density Trench MOSFETs with Self-Aligned N ⁺ /P ⁺ Source Formed on the Trench Side Wall", ISPSD-2003 Proceedings, pp. 1-4.						
	5.	M.A.A. In 'tZandt, et al., "Record-low 4mΩ mm ² specific on-resistance for 20V Trench MOSFETs", ISPSD-2003 Proceedings, pp. 1-4.						
	6.	Mohamed Darwish et al., "A New Power W-Gated Trench MOSFET (WMOSFET) with High Switching Performance", ISPSD-2003 Proceedings, pp 1-4.						
	7.	Syotaro Ono et al., "30V New Fine Trench MOSFET with Ultra Low On-Resistance", ISPSD-2003 Proceedings, pp. 1-4.						

Examiner: 	Date Considered: 11/26/05
* Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication with applicant.	